

# MAPRST1214-150UF



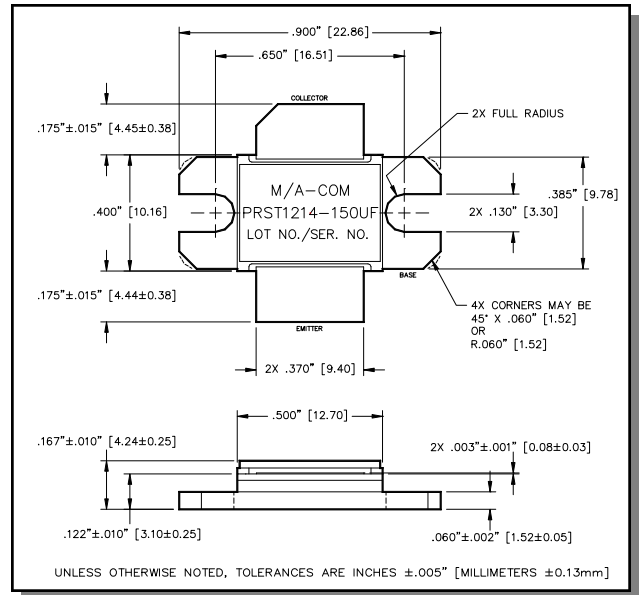
Radar Pulsed Power Transistor  
150W, 1.2-1.4 GHz, 6ms Pulse, 25% Duty

M/A-COM Products  
Released, 30 May 07

## Features

- NPN silicon microwave power transistors
- Common base configuration
- Broadband Class C operation
- High efficiency inter-digitized geometry
- Diffused emitter ballasting resistors
- Gold metallization system
- Internal input and output impedance matching
- Hermetic metal/ceramic package
- RoHS compliant

## Outline Drawing



## Absolute Maximum Ratings at 25°C

Parameter	Symbol	Rating	Units
Collector-Emitter Voltage	$V_{CES}$	70	V
Emitter-Base Voltage	$V_{EBO}$	4.0	V
Collector Current (Peak)	$I_C$	19.5	A
Power Dissipation @ +25°C	$P_{TOT}$	580	W
Storage Temperature	$T_{STG}$	-65 to +200	°C
Junction Temperature	$T_J$	200	°C

## Electrical Specifications: $T_C = 25 \pm 5^\circ\text{C}$ (Room Ambient)

Parameter	Test Conditions	Frequency	Symbol	Min	Max	Units
Collector-Emitter Breakdown Voltage	$I_C = 10\text{mA}$		$BV_{CES}$	70	-	V
Collector-Emitter Leakage Current	$V_{CE} = 40\text{V}$		$I_{CES}$	-	4.0	mA
Thermal Resistance	$V_{CC} = 36\text{V}$ , $P_{in} = 27\text{W}$	$F = 1.2, 1.3, 1.4\text{ GHz}$	$R_{TH(JC)}$	-	0.3	°C/W
Output Power	$V_{CC} = 36\text{V}$ , $P_{in} = 27\text{W}$	$F = 1.2, 1.3, 1.4\text{ GHz}$	$P_{OUT}$	150	-	W
Power Gain	$V_{CC} = 36\text{V}$ , $P_{in} = 27\text{W}$	$F = 1.2, 1.3, 1.4\text{ GHz}$	$G_P$	7.4	-	dB
Gain Flatness	$V_{CC} = 36\text{V}$ , $P_{in} = 27\text{W}$	$F = 1.2, 1.3, 1.4\text{ GHz}$	$\Delta G$	-	1.25	dB
Collector Efficiency	$V_{CC} = 36\text{V}$ , $P_{in} = 27\text{W}$	$F = 1.2, 1.3, 1.4\text{ GHz}$	$\eta_C$	45	-	%
Input Return Loss	$V_{CC} = 36\text{V}$ , $P_{in} = 27\text{W}$	$F = 1.2, 1.3, 1.4\text{ GHz}$	RL	-	-9	dB
Pulse Droop	$V_{CC} = 36\text{V}$ , $P_{in} = 27\text{W}$	$F = 1.2, 1.3, 1.4\text{ GHz}$	Droop	-	0.5	dB
Load Mismatch Tolerance	$V_{CC} = 36\text{V}$ , $P_{in} = 27\text{W}$	$F = 1.2, 1.3, 1.4\text{ GHz}$	VSWR-T	-	3:1	-
Load Mismatch Stability	$V_{CC} = 36\text{V}$ , $P_{in} = 27\text{W}$	$F = 1.2, 1.3, 1.4\text{ GHz}$	VSWR-S	-	1.5:1	-

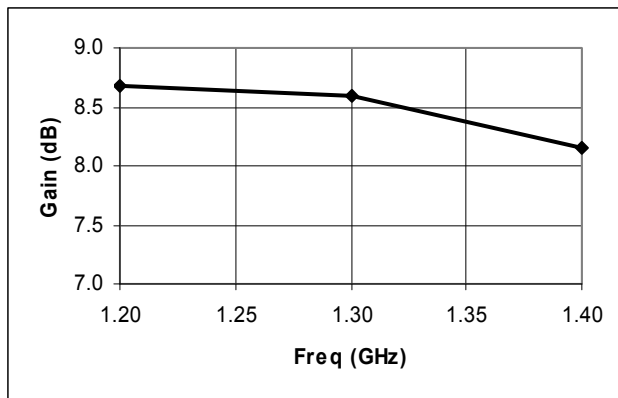
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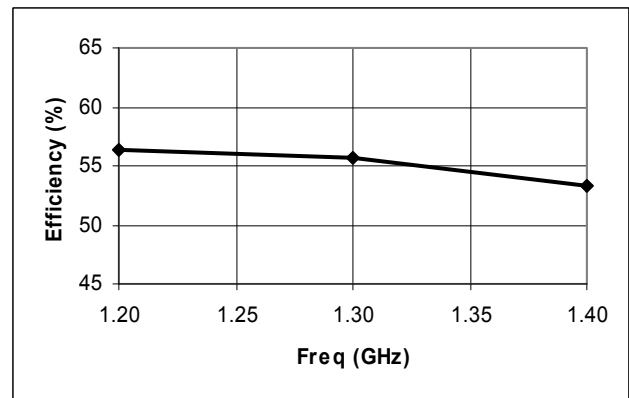
## Typical RF Performance

Freq. (GHz)	Pin (W)	Pout (W)	Gain (dB)	Ic (A)	Eff (%)	Droop (dB)	RL (dB)	VSWR-S (1.5:1)	VSWR-T (3:1)
1.2	27	199	8.67	9.81	56.4	0.08	-11.3	S	P
1.3	27	196	8.60	9.76	55.8	0.13	-18.8	S	P
1.4	27	176	8.15	9.19	53.3	0.12	-16.0	S	P

## Gain vs. Frequency



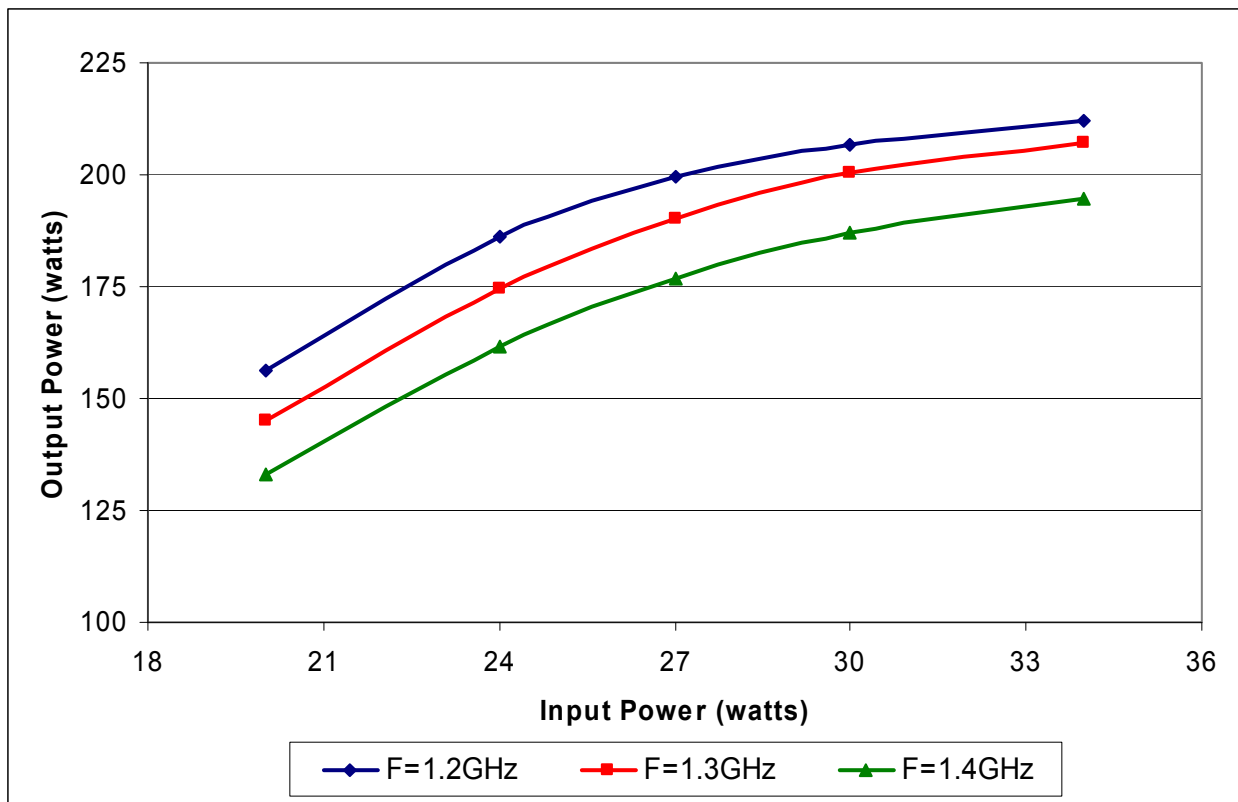
## Collector Efficiency vs. Frequency



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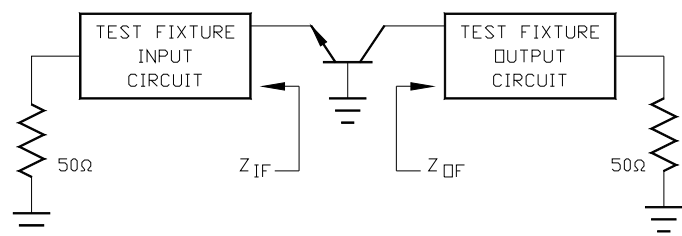
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## RF Power Transfer Curve (Output Power Vs. Input Power)



## RF Test Fixture Impedance

F (GHz)	Z <sub>IF</sub> (Ω)	Z <sub>OF</sub> (Ω)
1.2	1.7 - j1.8	2.0 - j2.3
1.3	1.6 - j1.3	1.95 - j2.0
1.4	1.4 - j1.0	1.8 - j1.85



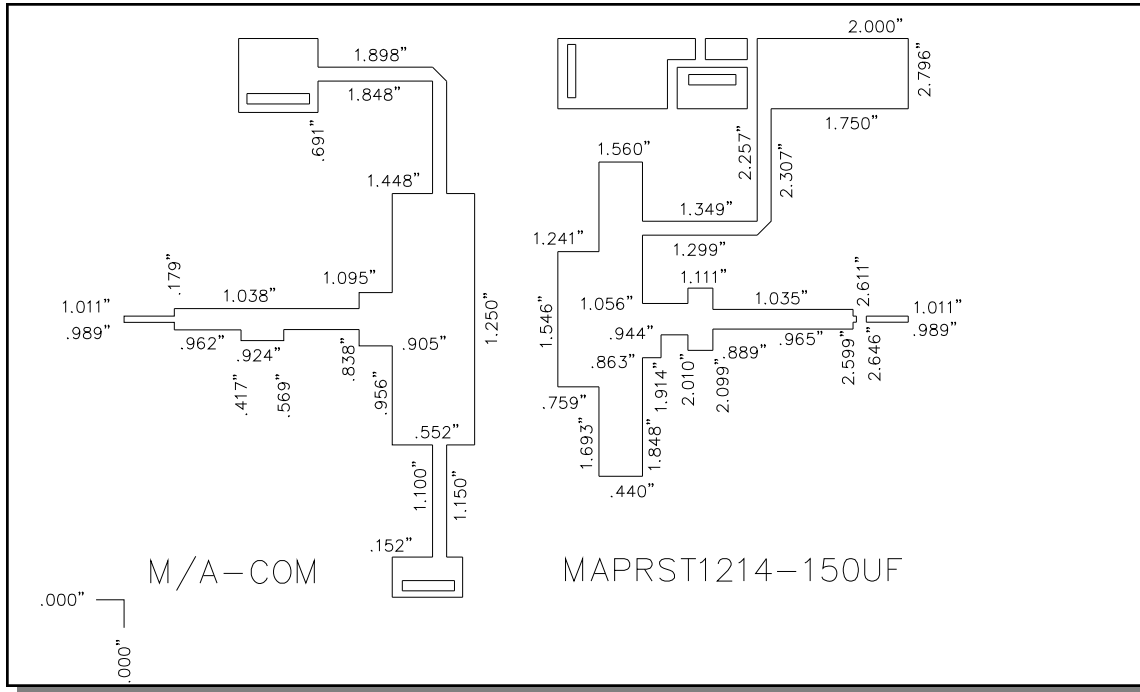
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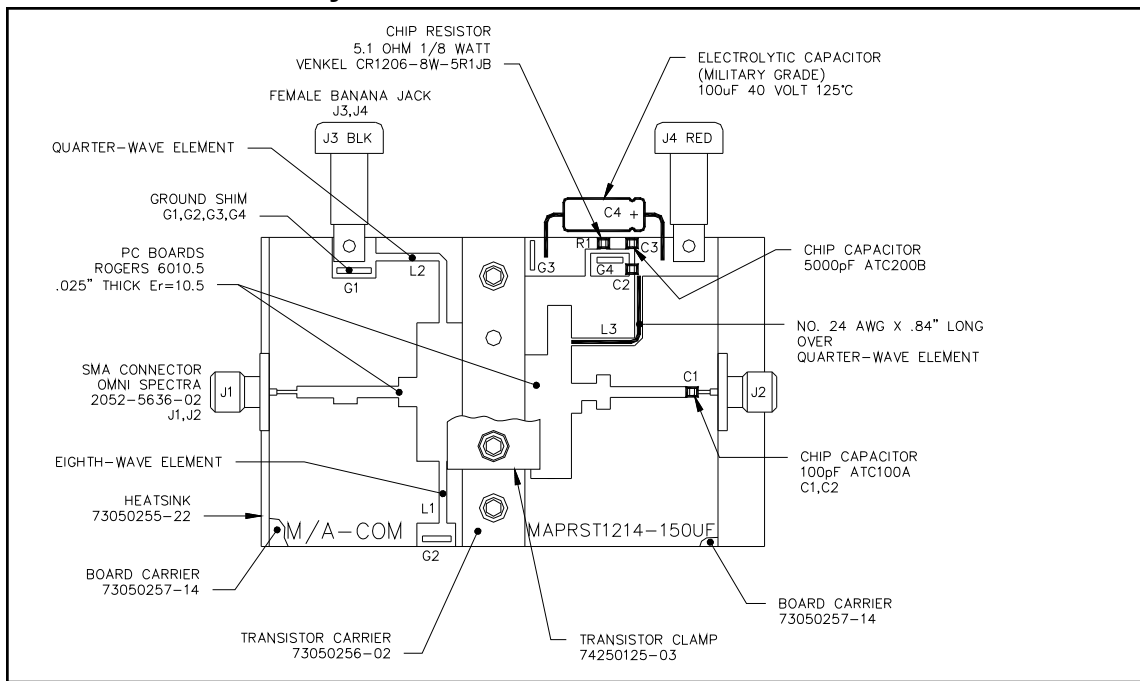
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## Test Fixture Circuit Dimensions



## Test Fixture Assembly



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